

Preliminary test beam results of SOI monolithic pixel detector

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BEAM TELESCOPE AND TEST BEAM WORKSHOP
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1 SOI technology for monolithic pixel design

2 System characterization

- SOI prototype chip overview
- Testbeam setup

3 Measurement results

- Correlation with telescope
- Energy distribution
- Clusterization methods
- Position reconstruction
- Alignment correction
- Spatial resolution

4 Summary

Monolithic pixel detectors in SOI

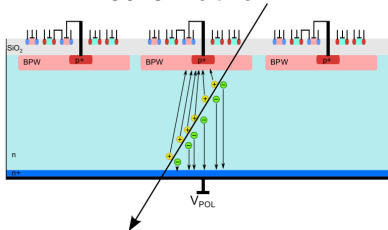
Properties

- Minimum pitch $< 10 \mu m$
- Small sensor capacitance (good SNR)
- Double SOI \rightarrow radiation hardness
- Wide temperature range (4 – 400K)
- Thinner and cheaper than hybrid solutions

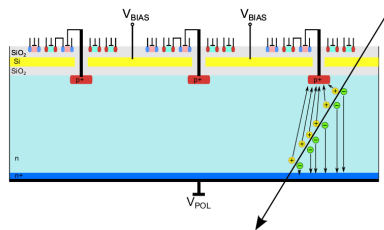
Double Silicon-On-Insulator

- voltage applied on Mid-Si layer allows to correct the potential changes caused by positive charges induced by irradiation,
- Mid-Si shields electronic from negative influence of high voltage needed for fully depletion.

SOI STRUCTURE



DOUBLE SOI STRUCTURE



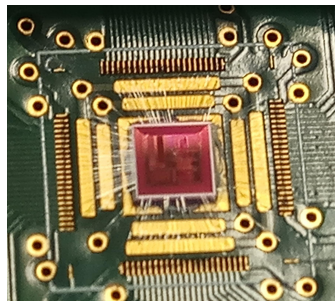
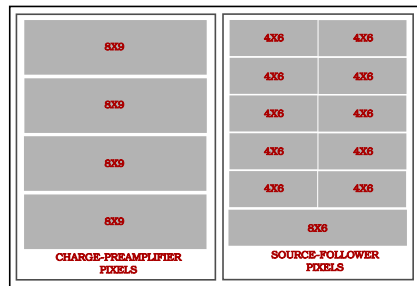
Lapis 200 nm Fully-Depleted Low-Leakage SOI CMOS with four wafer types: FZ(n), CZ(n), FZ(p) and Double SOI(p)

Architecture of SOI prototype chip

- submatrixes with different source-followers and charge pre-amplifiers, various layouts and transistor sizes,
- in total 16×36 pixels,
- $30 \mu m \times 30 \mu m$ pixel size $\rightarrow \sim 0.52 \text{ mm}^2$ matrix area,
- rolling shutter readout (integration time for one frame: $150 \mu s$),
- different wafer types (**FZ(n)**, **CZ(n)**, **FZ(p)** **Double SOI**) with different substrate thickness ($300\text{-}500 \mu m$) and resistivity ($2k\Omega$, 700Ω , $8k\Omega$),
- technology allows to fabricate thin wafer - down to $50 \mu m$.

For this study only source-follower pixels were used on FZ(n) wafer.

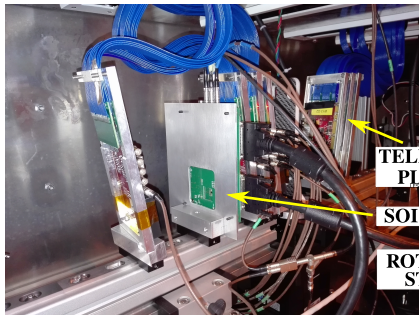
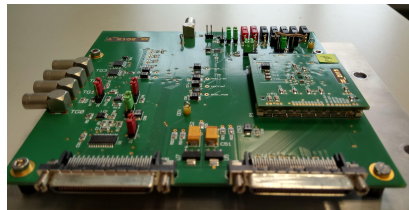
Very small size of submatrixes (different gain, noise) worsens achievable position resolution.



Testbeam setup

DAQ setup:

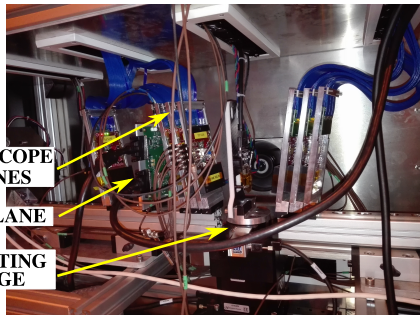
- main readout PCB + mezzanine boards with different SOI chips
- FPGA - PC → Ethernet
- DAQ Software - ROOT 6
- possibility of automatic parameters scans
- **TESTBEAM:** in the CLICdp Timepix3 telescope in the SPS-H6 beamline



TELESCOPE
PLANES

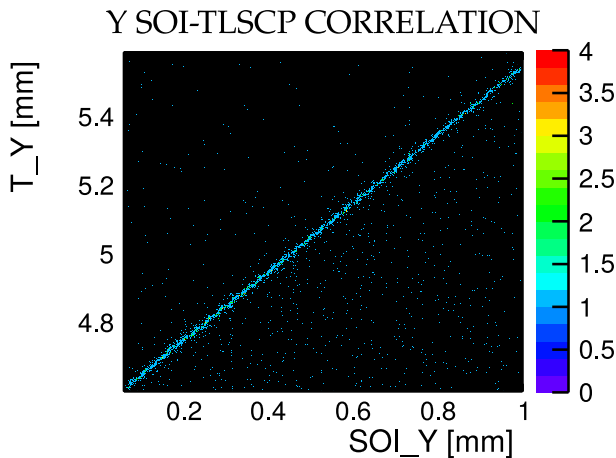
SOI PLANE

ROTATING
STAGE



More details about SOI-telescope integration see [Andreas Nurnberg Wednesday talk "Data-taking experience with the CLICdp Timepix3 telescope"](#)

Correlation with telescope

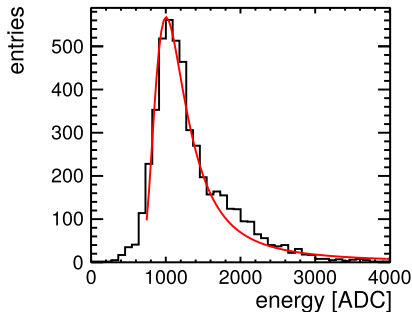


- good correlation with telescope
- large background due to long integration time of SOI pixel

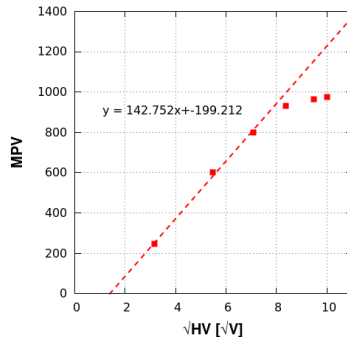
Energy spectrum

- Landau energy spectra of SOI hits after clusterization. Plot shows all hits (before track association).
- The low energy tail most probably comes from readout issues.
- MPV signal saturates above 80V (default biasing was 90V).

SOI HITS ENERGY SPECTRUM



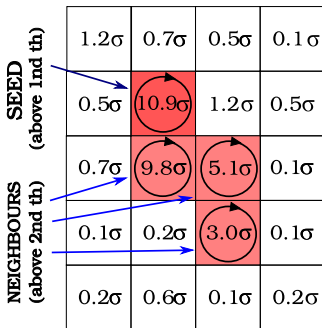
MPV vs HV



Clusterization methods

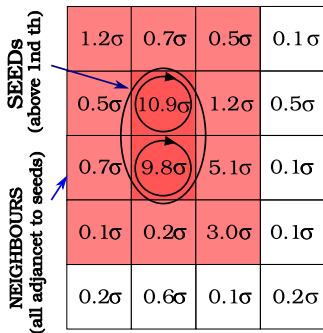
Different methods of clusterization in order to improve position calculation:

TWO-SEED METHOD



- Find pixels with signal above first threshold (signal $> 9\sigma = 9 \times$ pixel noise)
- Find all adjacent pixels above second threshold (signal $> 2\sigma$)
- When any pixel found, repeat algorithm for each new one.
- 4-pixel cluster is found.

ALL-ADJANECT METHOD

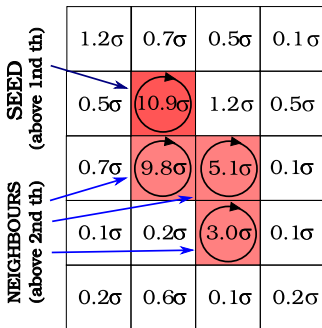


- Find pixel with signal above threshold (signal $> 9\sigma$)
- When seed found, found all next adjacent seeds and repeat for each new one.
- Add to cluster all seeds neighbours
- 12-pixel cluster found.

Clusterization methods

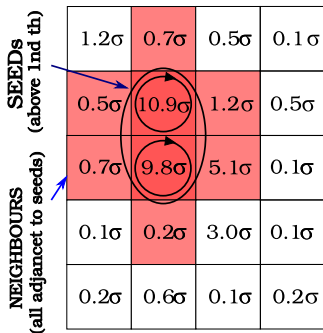
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CROSS METHOD

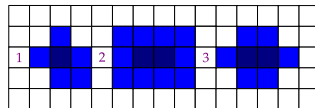


- Find pixel with signal above threshold (signal $> 9\sigma$)
- When seed found, found all next adjacent seeds and repeat for each new one.
- Add to cluster all seeds neighbours in "cross" pattern
- 8-pixel cluster found.

Clusterization methods comparison

Two-seed method

- mean cluster size: 3.7 pixels
- asymmetry in resolution in x and in y direction



All-adjacent method

- mainly 2-seed clusters (50%), 1-seed cluster (36%)
- about 80% less reconstructed clusters then in two-seed methods
- resolution in x and in y consistent
- threshold condition used: $30 \times \text{pixel noise}$ (around 500 ADC) \rightarrow high, but it is still 30% of most energetic pixel in cluster

Cross method

- similar to all-adjacent, but does not take neighbours on diagonal to seed.
- gives the same results as all-adjacent method

Conclusion

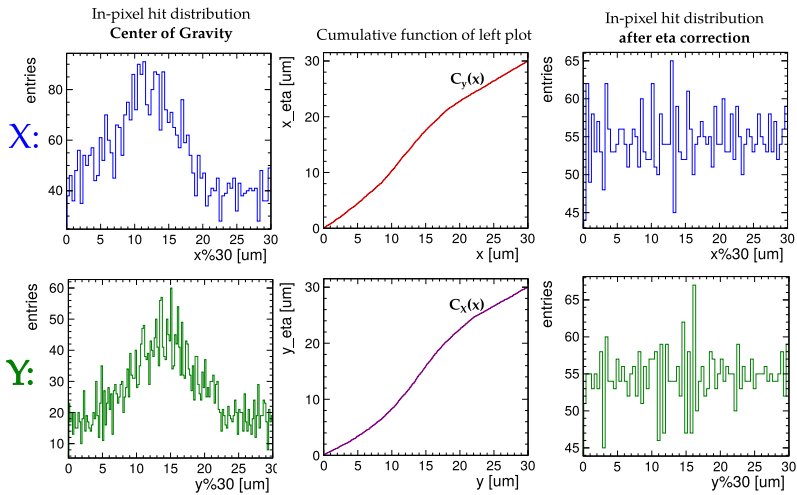
Two-seed method gives the best results in case of energy resolution, but the worse for spatial resolution. All-adjacent and cross methods are the best for position reconstruction, but give pure energy resolution.

Position reconstruction

For position reconstruction two methods were tested:

- ① Center of Gravity
- ② Eta correction

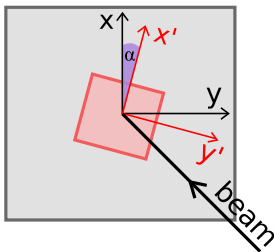
The in-pixel distribution is plotted → the cumulative function of this distribution is calculated: $C_X(x) \rightarrow$ the corrected position x_{ETA} is given by: $x_{ETA} = C_X(x_{COG})$, where x_{COG} is the hit position obtained from center of gravity method.



Alignment of SOI pixel chip

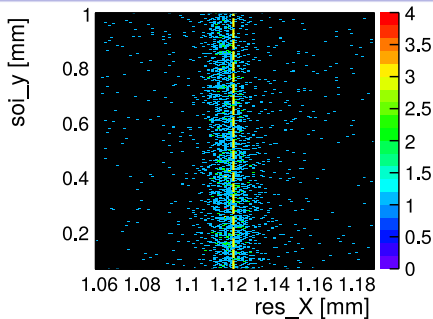
Two alignment methods were applied:

- ① slope of soi y hit position versus residuum x,
- ② minimum residuum versus rotation angle.

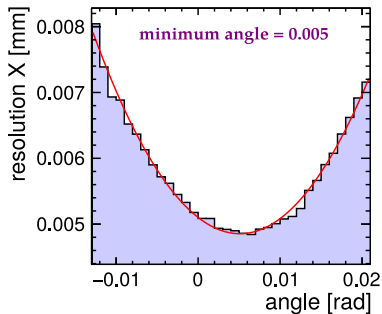


- both methods gave the same angle
- rotation angle is:
 $\alpha_{rot} = 0.005 \text{ [rad]} = 0.285 \text{ [deg]}$

1 METHOD:

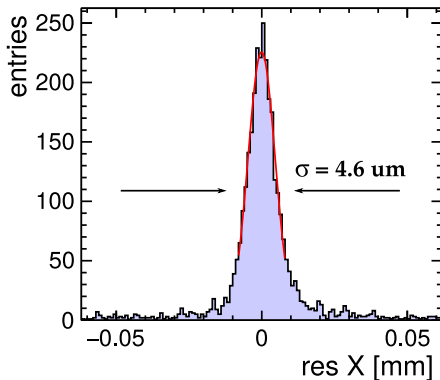


2 METHOD:



Spatial resolution of SOI detector - 90V FZ(n)

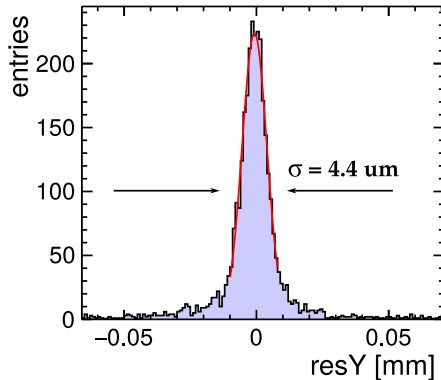
SOI RESOLUTION X



all-adjacent, rotation, eta - X

$$X_{\text{res}} = 4.6 \mu\text{m}$$

SOI RESOLUTION Y



all-adjacent, rotation, eta - Y

$$Y_{\text{res}} = 4.4 \mu\text{m}$$

Taking into account the telescope resolution ($\sigma_T = \sim 2\mu\text{m}$) the SOI resolution is around $\sigma_{\text{SOI}} = \sim 4\mu\text{m}$.

Summary

- ① The SOI pixel detector was tested successfully **for the first time in CLICdp testbeam.**
- ② Data analysis including clustering, eta correction and alignment was performed in order to calculate the spatial resolution.
- ③ **Spatial resolution for 30 μm SOI pixels of around 4 μm was obtained.**
- ④ Ongoing studies: resolution vs bias voltage, analysis for different wafers.

Close future plans:

- New SOI prototype with larger and more uniform matrix has been fabricated and will be tested in the next testbeam.
- Next chip with timing information is being developed.

THANK YOU FOR ATTENTION !